di-men-sion (d@m ாடுhடு), di}) noun

## Abbr. dim.

- 1. A measure of spatial extent, especially width, height, or length.
- 2. Often dimensions. Extent or magnitude; scope: a problem of alarming dimensions.
- 3. Aspect; element: "He's a good newsman, and he has that extra dimension" (William S. Paley).
- 4. Mathematics. a. One of the least number of independent coordinates required to specify uniquely a point in space or in space and time. b.

  The range of such a coordinate.
- 5. Physics. A physical property, such as mass, length, time, or a combination thereof, regarded as a fundamental measure or as one of a set of fundamental measures of a physical quantity: Velocity has the dimensions of length divided by time.

#### verb, transitive

di-men-sioned, di-men-sion-ing, di-men-sions

- 1. To cut or shape to specified dimensions.
- 2. To mark with specified dimensions.

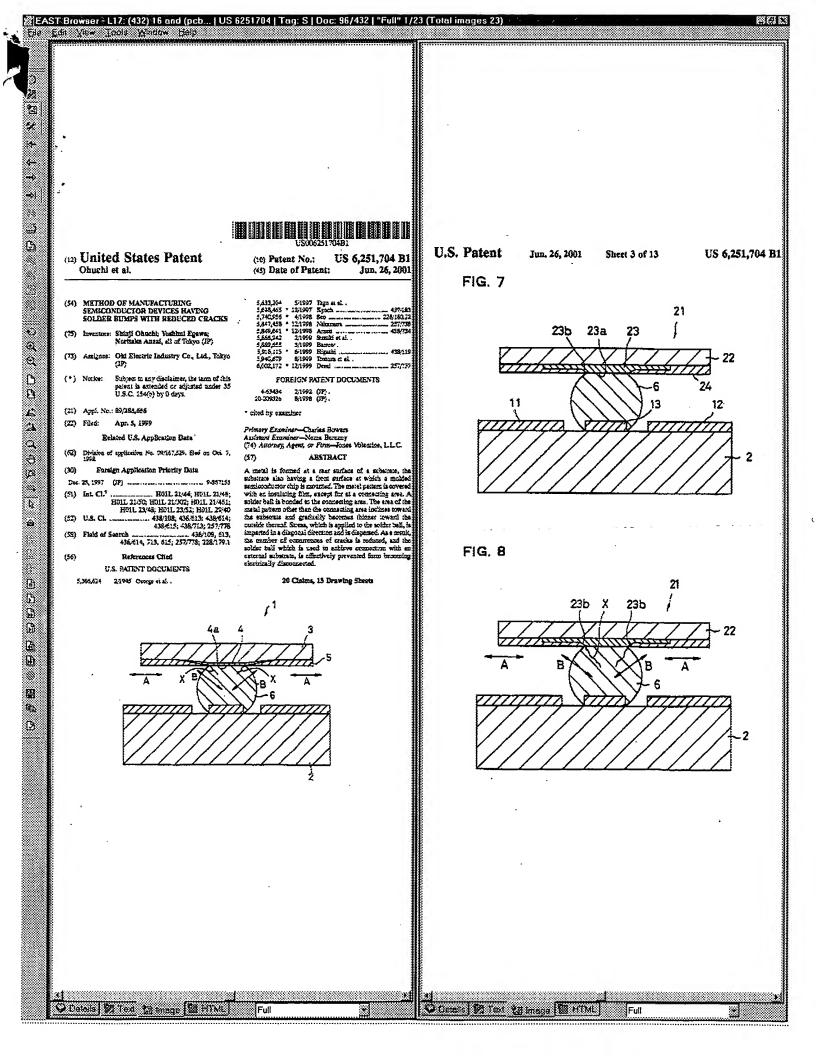
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prox-l-mate (prikilsii-mill) adjective

- 1. Closely related in space, time, or order; <u>Verylnears</u> See synonyms at close.
- 2. Approximate.

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## METHOD OF MANUFACTURING SEMICONDUCTOR DEVICES HAVING SOLDER BUMPS WITH REDUCED CRACKS

# CROSS REFERENCE TO RELATED APPLICATIONS

This is a divisional application of application Ser. No. 09/167,529, filed Oct. 7, 1998, which is hereby incorporated by reference in its entirety for all purposes.

#### BACKGROUND OF THE INVENTION

1. Field of the Invention

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The present invention relates to a semiconductor device and a manufacturing method thereof.

2. Description of Related Art

With the rapid advent of portable devices such as mobile phones and IC cards in recent years, and the resulting need for thinner, lighter, more compact resin-scaled semiconductor devices to be mounted in those devices, a great number of means to fulfill such need have been proposed in the prior art. In one such instance, a method for mounting a resinsealed semiconductor device 101 at an external substrate 102 such as a printed circuit board, as illustrated in FIG. 31, is proposed.

In the resin-sealed semiconductor device 101 that achieves this mounting state, a mold portion 104 constituted by sealing a semiconductor chip is provided at a front surface of a substrate 103 constituted of an epoxy resin, ceramic or the like and solder balls 105 to function as solder bumps are bonded in advance at specific connecting areas at a rear surface of the substrate 103. Then, the semiconductor device 101 in this state is placed on the external substrate 102 and the entire assembly is placed in an atmosphere at a temperature ranging approximately from 220 centigrade to 240 centigrades. Thus, the solder balls 105 are at least partially melted so that the semiconductor device 101 can be mounted at the external substrate 102. Through this mounting method, electrical characteristics with a low capacity and low inductance are achieved.

To describe the structure of the resin-sealed semiconductor device 101 that achieves this mounting state in more detail, in reference to FIG. 32, a metal pattern 106 formed at a rear surface of the substrate 103 is covered with an insulating film 107 constituted of, for instance, asolder resist, except at a specific connecting area 106a, the connecting area 106a is set so that it lies flush with a front surface of the insulating film 107 and a surface of the connecting area 106a is flat. A solder ball 105 is bonded to the connecting area 106a.

When mounting the semiconductor device 101 at the external substrate 102, the solder ball 105 is aligned at a specific electrode portion 109 formed between insulating layers 108 and 108 and then the entire assembly is placed in 55 a specific heated atmosphere in this state.

However, the following problem manifests with the semiconductor device 101 in the prior art structured as described above in a reliability test which is performed after it is mounted at the external substrate 102. Namely, during the reliability test in which the semiconductor device is exposed to an atmosphere at room temperature or within the range of -65 centigrade to 150 centigrade, an electrical disconnection sometimes occurs at the solder balls 105. This is considered to be caused by the difference between the coefficients of 65 thermal expansion of the semiconductor device 101 constituted of the substrate 103 and the mold portion 104 and of 2

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the external substrate 102 at which the semiconfuctor device 101 is mounted, which causes the semiconfuctor device 101 to be stretched and to contract, as illustrated in FIG. 33, causing cracks 110 and 111 to be formed at a solder ball 108, which, in turn, leads to degradation of the electrical characteristics and eventually to disconnection as these cracks 110 and 111 grow to link with each other.

In an examination of the positions at which the cracks 110 and 111 are formed, their patierns and their directions, conducted by the inventors of the present invention, cracks were found to form near the metal pattern 106 to extend in parallel to the metal pattern 106 in most instances. The inventors of the present invention conducted a similar experiment after essentially modifying the shape of the metal pattern connecting area which is bonded with the solder ball, and a great improvement was observed.

#### SUMMARY OF THE INVENTION

A first object of the present invention, which has been completed by addressing the problem of the semiconductor devices and the manufacturing method thereof in the prior art, is to provide a new and improved semiconductor device with which it is possible to reduce the number of cracks that are formed compared to the prior an and even when they are formed, they are formed and extend in a direction in which disconnection does not readily occur.

A second object of the present invention is to provide a method for manufacturing such a semiconductor device.

In order to achieve the first object of the present invention, in a first aspect of the present invention, a semiconductor device is provided with a substrate having a semiconductor chip at a front surface thereof and a conductor pattern formed at a rear surface of the substrate, i.e., at the mounting surface, with the conductor pattern covered with an insulating film except at specific connecting areas and solder bumps bonded to the connecting areas, which is characterized in that the area of the conductor pattern outside the connecting areas covered by the insulating film inclines toward the substrate, is provided.

An examination conducted by the inventors of the present invention verified that with the area of the conductor pattern such as a metal pattern covered with the insulating film outside the connecting areas made to incline toward the substrate, the rate of cracking is reduced and that even when a crack is formed, it extends almost along the inclination, i.e., in a diagonal direction. These results are assumed to be attributable to the stress at the solder bumps such as solder balls occurring in a diagonal direction and being dispersed, caused by the difference between the coefficients of thermal expansion described earlier. Thus, with the rate of cracking reduced, degradation in the electrical characteristics can be prevented, and furthermore, even when a crack occurs, it extends in a diagonal direction and, consequently, disconnections are greatly reduced too.

In the semiconductor device achieving the advantages described above, the area of the conductor pattern covered by the insulating film outside the connecting areas can be formed so that it becomes gradually thinner, as well as inclining toward the substrate. Furthermore, the portions of the rear surface of the substrate that correspond to the connecting areas may be distended toward the solder bumps, with the insulating film that conforms to the distended shape.

In addition, in order to achieve the object described above, in a second aspect of the present invention, a semiconductor device is provided with a substrate having a semiconductor chip at a front surface thereof and a conduc-

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which is used to achieve connection with an external substrate, is effectively prevented form becoming electrically disconnected.

20 Claims, 33 Drawing figures

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Exemplary Claim Number:

Number of Drawing Sheets:

BRIEF SUMMARY:

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- (1) BACKGROUND OF THE INVENTION
- 1. Field of the Invention
- The present invention relates to a semiconductor device and a manufacturing method thereof.
- Description of Related Art (4)
- With the rapid advent of portable devices such as mobile phones and IC cards in recent years, and the resulting need for thinner, lighter, more compact resin-sealed semiconductor devices to be mounted in those devices, a great number of means to fulfill such need have been proposed in the prior art. In one such instance, a method for mounting a resin-sealed semiconductor device 101 at an external substrate 102 such as a printed circuit board, as illustrated in FIG. 31, is proposed.
- In the resin-sealed semiconductor device 101 that achieves this mounting state, a mold portion 104 constituted by sealing a semiconductor chip is provided at a front surface of a substrate 103 constituted of an epoxy resin, ceramic or the like and solder balls 105 to function as solder bumps are bonded in advance at specific connecting areas at a rear surface of the substrate 103. Then, the semiconductor device 101 in this state is placed on the external substrate 102 and the entire assembly is placed in an atmosphere at a temperature ranging approximately from 220 centigrade to 240 centigrade. Thus, the solder balls 105 are at least partially melted so that the semiconductor device 101 can be mounted at the external substrate 102. Through this mounting method, electrical characteristics with a low capacity and low inductance are

€> Col 1, L 36-38 To describe the structure of the resin-sealed semiconductor device 101 that achieves this mounting state in more detail, in reference to FIG. 32, a metal pattern 106 formed at a rear surface of the substrate 103 is covered with an insulating film 107 constituted of, for instance, asolder resist, except at <u>a specific connecting area 106a, the</u> FULL

omitted in the figures showing subsequent embodiments, too.

The semiconductor device 1 has a basic structure in which a metal pattern 4 constituting a conductor pattern is formed at a rear surface of the substrate

3 and a front surface of the metal pattern 4
is covered with an insulating film 5 except for the connecting area 4a. The solder ball 6, which constitutes a solder bump, is bonded at the connecting area 4a. It is to be noted that the planar shape of the connecting area 4a is circular.

- The area other than the connecting area 4a in the metal pattern 4 of the semigonductor device 1, i.e., the area covered with the insulating film 5, inclines toward the substrate 3, and furthermore, the thickness of the metal pattern 4 is gradually reduced toward the outside. In addition, the rear surface of the substrate 3 is formed to lie along the shape of the metal pattern 4. In other words, the portion that corresponds to the connecting area 4a is formed in a shape constituting a three-dimensional convex curve toward the solder ball 6.
- The semiconductor device 1 in the first embodiment, which is structured as described above is mounted at the external substrate 2 in a manner identical to that employed in the prior art described earlier, by aligning the solder ball 6 at a specific electrode portion 13 formed between insulating layers 11 and 12 that are formed at a front surface of the external substrate 2 and by placing the whole assembly in a specific heated atmosphere to mount the semiconductor device through connection at the solder ball 6.
- Even when the semiconductor device 1 in the first embodiment is placed in an atmosphere in which the temperature changes drastically during a reliability test conducted after it is mounted at the external substrate 2 and the difference between the coefficients of thermal expansion at the semiconductor device 1 and the external substrate 2 causes a force in the horizontal direction due to stretching, contraction and the like to be applied to the semiconductor device 1 as indicated with the reciprocal arrows A in FIG. 2, resulting in stress applied to the solder ball 6 connecting the semiconductor device 1 and the external substrate 2, the stress is applied along the inclined portion of the metal pattern 4 as indicated by the reciprocal arrows B in FIG. 2. Moreover, the stress is applied radially over the entire circumference, and therefore, is dispersed.

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is mounted at an external substrate 2 such as a wiring board, and in order to facilitate the explanation, the illustration of a molded semiconductor chip mounted on a substrate 3 in the semiconductor device 1 is omitted. It is to be

noted that an illustration of a molded semiconductor chip on the substrate is omitted in the figures showing subsequent embodiments, too.

- (4) The semiconductor device 1 has a basic structure in which a metal pattern 4 constituting a conductor pattern is formed at a rear surface of the substrate 3 and a front surface of the metal pattern 4 is covered with an insulating film 5 except for the connecting area 4a. The solder ball 6, which constitutes a solder bump, is bonded at the connecting area 4a. It is to be noted that the planar shape of the connecting area 4a is circular.
- (5) The area other than the connecting area 4a in the metal pattern 4 of the semiconductor device 1, i.e., the area covered with the insulating film 5, inclines toward the substrate 3, and furthermore, the thickness of the metal pattern 4 is gradually reduced toward the outside. In addition, the rear surface of the substrate 3 is formed to lie along the shape of the metal pattern 4. In other words, the portion that corresponds to the connecting area 4a is formed in a shape constituting a three-dimensional convex curve toward the solder ball 6.
- (6) The semiconductor device 1 in the first embodiment, which is structured as described above is mounted at the external substrate 2 in a manner identical to that employed in the prior art described earlier, by aligning the solder ball 6 at a specific electrode portion 13 formed between insulating layers 11 and 12 that are formed at a front surface of the external substrate 2 and by placing the whole assembly in a specific heated atmosphere to mount the semiconductor device through connection at the solder ball 6.
- (7) Even when the semiconductor device 1 in the first embodiment is placed in an atmosphere in which the temperature changes drastically during a reliability test conducted after it is mounted at the external substrate 2 and the difference between the coefficients of thermal expansion at the semiconductor device 1 and the external substrate 2 causes a force in the horizontal direction due to stretching, contraction and the like to be applied to the semiconductor device 1 as indicated with the reciprocal arrows A in FIG. 2,

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U.S. Patent Jun. 26, 2001 Sheet 1 of 13 US 6,251

FIG. 1

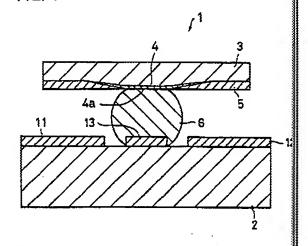
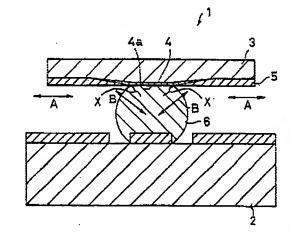


FIG. 2



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Next, as illustrated in FIG. 5, a ceramic plate 15 having an empty portion 15a over the area corresponding to the connecting area 4a is placed at a specific position. Then, pressure is applied to the entire rear surface of the substrate 3 in the direction indicated by the arrows in the figure. This causes the crushed metal pattern 4 to enter a gap "d" formed by the thickness of the metal pattern 4 between the substrate 3 and the ceramic plate 15. Ιn addition, since no force is applied to empty portion 15a formed at the ceramic plate 15 in corresponding connecting area 4a, only the area other than the area at the substrate, corresponding to the empty portion 15a is compressed.

Consequently, a structure in which the area other than the connecting area 4a in the metal pattern 4, i.e., the area covered with the insulating film 5 constituted of the ceramic 15 is made to incline toward the substrate 3 and the thickness of the metal pattern 4 is gradually reduced toward the outside, as illustrated in FIG. 6, is achieved. addition, the rear surface of the substrate 3 achieves a shape that conforms to the shape of the metal pattern 4. After this, a semiconductor chip is mounted at a front surface of the substrate 3 and then is molded with resin or the like. The semiconductor device 1

illustrated in FIG. 1 is then completed by bonding a solder ball 6 to the connecting area 4a through a method in the known art. Thus, the semiconductor device 1 in the first embodiment can be manufactured with a high degree of efficiency.

Next, the semiconductor device in a second embodiment is explained. the state achieved by mounting the semiconductor device at the external substrate 2 in FIG. 7 clearly illustrates, the members constituting the basic structure at a rear surface of a substrate 22 of the semiconductor device 21 in the second embodiment are identical to those in the semiconductor device 1 in the first embodiment, with a metal pattern 23 constituting a conductor pattern formed at a rear surface of the substrate 22 and an insulating film 24 covering a front surface of the metal pattern 23 except for a connecting area 23a. The planar shape of the connecting area 23a is circular.

A staged portion 23b is formed in the area between the connecting area 23a and the area covered with the insulating film 24 in the metal pattern 23 at the semiconductor device 21, and the staged portion 23b is formed in a tapered shane In other words Deteis \$5 Text (1) image \$1 HTML

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omitted in the figures showing subsequent embodiments, too.

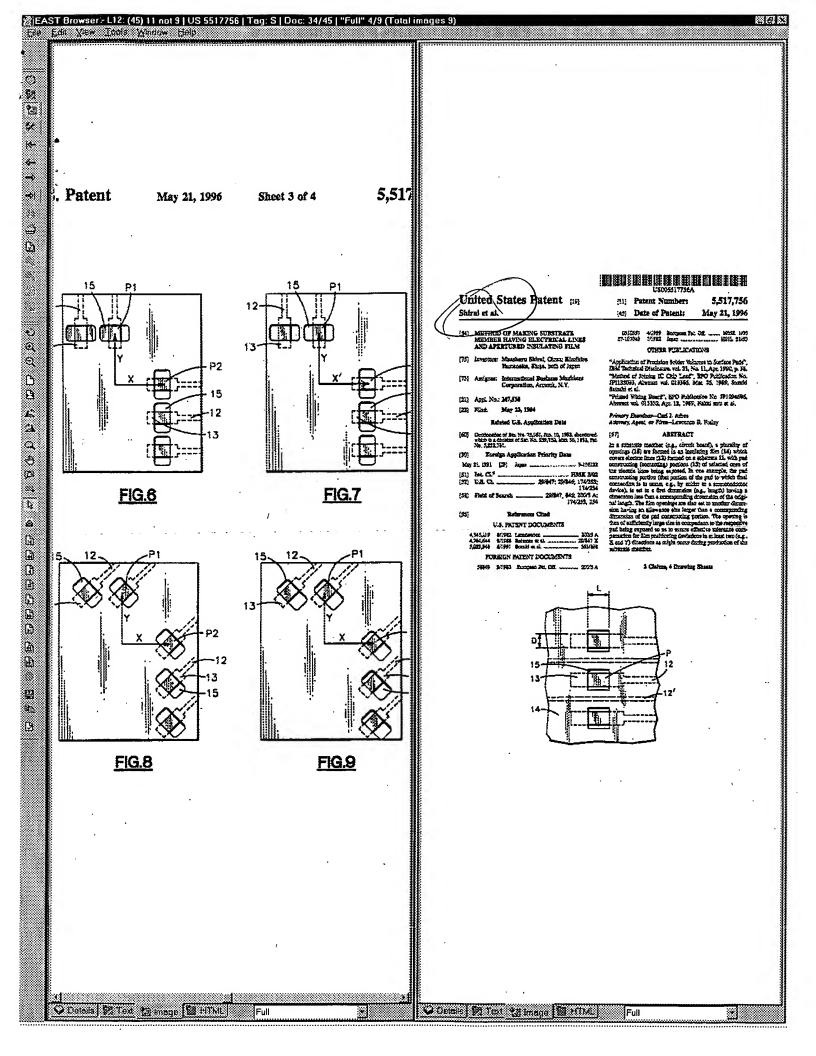
The semiconductor device 1 has a basic structure in which a metal pattern 4 constituting a conductor pattern is formed at a rear surface of the substrate

3 and a front surface of the metal pattern 4 is covered with an insulating film 5 except for the connecting area 4a. The solder ball 6, which constitutes a solder bump, is bonded at the connecting area 4a. It is to be noted that the planar shape of the connecting area 4a is circular. 76/10, 6/19-7

- The area other than the connecting area 4a in the metal pattern 4 of the semiconductor device 1, i.e., the area covered with the insulating film 5, inclines toward the substrate 3, and furthermore, the thickness of the metal pattern 4 is gradually reduced toward the outside. In addition, the rear surface of the substrate 3 is formed to lie along the shape of the metal pattern 4. In other words, the portion that corresponds to the connecting area 4a is formed in a shape constituting a three-dimensional convex curve toward the solder ball 6.
- The semiconductor device 1 in the first embodiment, which is structured as described above is mounted at the external substrate 2 in a manner identical to that employed in the prior art described earlier, by aligning the solder ball 6 at a specific electrode portion 13 formed between insulating layers 11 and 12 that are formed at a front surface of the external substrate 2 and by placing the whole assembly in a specific heated atmosphere to mount the semiconductor device through connection at the solder ball 6.
- Even when the semiconductor device 1 in the first embodiment is placed in an atmosphere in which the temperature changes drastically during a reliability test conducted after it is mounted at the external substrate 2 and the difference between the coefficients of thermal expansion at the semiconductor device 1 and the external substrate 2 causes a force in the horizontal direction due to stretching, contraction and the like to be applied to the semiconductor device 1 as indicated with the reciprocal arrows A in FIG. 2, resulting in stress applied to the solder ball 6 connecting the semiconductor device 1 and the external substrate 2, the stress is applied along the inclined portion of the metal pattern 4 as indicated by the reciprocal arrows B in FIG. 2. Moreover, the stress is applied radially over the entire circumference, and therefore, is dispersed.

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## METHOD OF MAKING SUBSTRATE MEMBER HAVING ELECTRICAL LINES AND APERTURED INSULATING FILM

The application is a continuation of application Ser. No. 3 08/075,067, filed Jun. 10, 1993, abandoned, which is a divisional of application Ser. No. 07/859,750 filed on Mar. 30, 1992, now U.S. Pat. 5,252,781.

# TECHNICAL FIELD

The invention relates to substrate members (e.g., circuit boards) including electric lines as part thereof and to a method of manufacturing such a substrate member. More particularly, the invention relates to a substrate member and method of making same wherein pads formed in conjunction with said lines and having predetermined areas in a predetermined positional relation are utilized while permitting a relative positional deviation between such pads (also referred to as pad constructing portions) of the electric lines and respective openings within an insulating film also used as part of the substrate member, the film functioning to cover selected portions of the line(s).

## DESCRIPTION

In a substrate member (e.g., printed circuit board) including electric lines, such electric (e.g., copper) lines are provided on a dielectric (e.g., fiberglass reinforced epoxy resin) substrate and an electrically insulating film may be provided on the substrate so as to cover the electric lines or portions thereof. To electrically connect the electric lines on the substrate to other circuits or components, openings may be formed in the insulating film in order to expose parts of the electric lines, such exposed line portions also being defined as "pads" (or pad constructing portions).

It is required that such pads be of specified area (large enough) in order to assure the reliability of the electrical connection. Particularly, in a small substrate such as a substrate having electric lines used to support (be coupled to) a semiconductor chip or the like (such exposed areas being extremely small), the exposed areas of the pad must be precisely defined. Moreover, in a flip-chip type of structure (wherein the pads on the substrate and the pads on the semiconductor chip typically used in such members are connected by a metal (e.g., solder) hall, not only are both of the paired pads electrically connected but also the semiconductor chip is physically positioned onto the substrate having such electric pads/lines, such that the area of the pad is also important in terms of providing sufficient strength for the final structure.

In the situation where a position of an opening formed in an insulating film is offset from an electric line pad constructing portion provided, e.g., at a front edge of an electric line, the resulting exposure area of the electric line pad may 55 to 5 small, such that the reliabilities of any electrical connection and attaching strength may be severely diminished.

Because a process to form an electric line onto the substrate and to precisely orient the insulating film onto the 60 substrate so as to precisely form an opening relative to each line/pad must be acquentially executed (e.g., the lines are formed on the dielectric substrate first, following which the film is positioned thereover), a possibility exists that the positional deviation between the line/pad constructing portion and the respective film opening as mentioned above may be extremely high.

Even if the positional deviation is of a degree such that only a part of the line/pad constructing portion is covered by the insulating film, the problem of the aforementioned poor reliabilities still exists. That is, even in the case where part of the pad constructing portion lies within the film opening, the portion of the insulative film over the electric line may also function as a connecting pad, together with the pad constructing portion. Therefore, the combined pad area fluctuates due to the above positional deviation.

FIGS. 10-13 are provided to better illustrate the above. In FIG. 10, for example, the underlying circuit line 1 terminates in a circular contacting portion (pad) 2 of a predetermined diameter smaller than the respective opening 4 in the dielectric film (3) located thereover. Should the opening he shifted slightly, as in FIG. 11, a relatively large substrate surface area under the opening remains exposed. This is further seen for a positional change as depicted in FIG. 12. To prevent the above, a relatively large, annular pad may be provided (FIG. 13) in combination with a smaller diameter film opening 4. Using such parameters, film positioning deviations (no greater than dimension A) are compensated for to assure that a suitable pad area will always remain exposed. This necessitutes, however, the defined provision of large pad sites, further reducing the chance for high density site arrays highly desired in today's information handling systems (computer) environments to which the present invention is particularly suited.

To solve the foregoing and related problems, an improved method of making a substrate member has been developed. It is believed that such a method, and the substrate member resulting therefrom, will constitute a significant advancement in the art.

## DISCLOSURE OF THE INVENTION

It is an object of the invention to provide a substrate member having electric lines in which even when a predetermined positional deviation of an opening formed in the member's insulating film relative to a pad constructing portion of the member's electric line(s) occurs, such deviation is acceptable and a pad of a predetermined area can be assured.

It is snother object of the invention to provide a methodof making a substrate member having electric lines wherein a plurality of pads are formed onto a substrate (e.g., at the end of electric lines), such that even when a positional deviation of the openings in the member's insulation film occurs, as mentioned above, the relative positioning relation between the pads is held relatively constant.

## BRIEF DESCRIPTION OF THE DRAWINGS

FIG. 1 is an exploded perspective view of a substrate member including electric lines according to an embodiment of the invention.

FIG. 2 is a plan view of the substrate member including electric lines according to an embodiment of the invention.

FIG. 3 is a plan view of a substrate including electric lines according to another embodiment of the invention.

FIG. 4 is a representative diagram illustrating a size of an electric line according to the invention.

FIG. 5 is a representative diagram illustrating a size of opening of an insulating film according to the invention.

FIG. 6 is a representative diagram illustrating an arrangement of pads according to one embodiment of the invention.

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